

RECEIVED
CENTRAL FAX CENTER
AUG 18 2006

Amendments to the Specification:

Please replace paragraph [0053] with the following amended paragraph:

[0053] A pad 652 is defined after top layer 602 is etched to form bonding pads 624 and 636. Pad 652 is separated by a distance AJ from bonding pads 624 and 636. Furthermore, bonding pad 636 is ~~separated from~~ has a width AK near gaps 609A and 609B by at least a distance AK.

Please replace paragraph [0074] with the following amended paragraph:

[0074] In one embodiment of the invention, the dimensions of device 600 are as follows:

Reference number	Dimension (in microns)
Width A of mirror 606	>1000 & <1200 (e.g., 1110)
Length B of mirror 606	>4000 & <5500 (e.g., 5000)
Width C of mirror gap 609	>150 & <350 (e.g., (250)
Length D of beam 612	>3000 & <9000 (e.g., 8000)
Width E of beam 612	>800 & <1400 (e.g., 1240)
Base width F of rotational comb teeth 616	>8 & <14 (e.g., 10.5)
End width G of rotational comb teeth 616	>4 & <10 (e.g., 6)
Length H of rotational comb teeth 616	>400 & <900 (e.g., 780)
Width I of spring 622	>20 & <60 (e.g., 50)
Length J of spring 622	>200 & <500 (e.g., 390)
Height K of bonding pads 626 and 632	>350 & <700 (e.g., 640)
Width L of bonding pads 626 and 632	>350 & <700 (e.g., 660)
Base width M of stationary comb teeth 634	>8 & <14 (e.g., 11.5)

End width N of stationary comb teeth 634	>4 & <10 (e.g., 7)
Length O of stationary comb teeth 634	>400 & <900 (e.g., 780)
Spacing P between rotational comb teeth 616 and stationary comb teeth 636	>8 & <14 (e.g., 11.5)
Base width Q of stationary comb teeth 674	>8 & <14 (e.g., 8)
End width R of stationary comb teeth 674	>4 & <10 (e.g., 7)
Length S of stationary comb teeth 674	>150 & <500 (e.g., 200)
Base width T of stationary comb teeth 675	>6 & <14 (e.g., 7.5)
End width U of stationary comb teeth 675	>4 & <10 (e.g., 7)
Length V of stationary comb teeth 675	>150 & <500 (e.g., 100)
Comb teeth pitch W	>30 & <50 (e.g., 40)
Distance X from stationary comb teeth 674 to centerline 615	>500 & <700 (e.g., 660)
Distance Y from stationary comb teeth 675 to centerline 615	>500 & <700 (e.g., 660)
Thickness Z of bottom wafer 802 used to form bottom layer 604	>450 & <550 (e.g., 525)
Thickness AA of top oxide layer 804 on bottom wafer 802	>1 & <2 (e.g., 1.5)
Thickness AB of bottom oxide layer 806 on bottom wafer 802	>1 & <2 (e.g., 1.5)
Height AC of anchoring pads 668 and 670 on	>300 & <450 (e.g., 400)

bottom layer 604	
Height AD of stationary comb teeth 674 and 675 on bottom layer 604	>250 & <450 (e.g., 300)
Thickness AE of top wafer 812 used to form top layer 602	>120 & <240 (e.g., 150)
Thickness AF of top oxide layer 814 on top wafer 812	>1 & <2 (e.g., 1.2)
Thickness AG of bottom oxide layer 816 on top wafer 812	>1 & <2 (e.g., 1.2)
Depth AH of separation trench 809 on bottom wafer 812	>120 & <240 (e.g., 180)
Minimum distance AJ from pad +52 <u>652</u> to any of pads 624 and 636	>120 & <240 (e.g., 200)
Distance <u>Width</u> AK from of pad 652 to 636 near gap 609 around the mirror	>400 (e.g., 250)
Number of springs	2 to 20 (e.g., 18)
Number of bonding pads connected to springs	2 to 10 (e.g., 10)
Total mirror thickness with rib	>240 (e.g., 675)
Total hinge length for one spring	>600 (e.g., 1900)